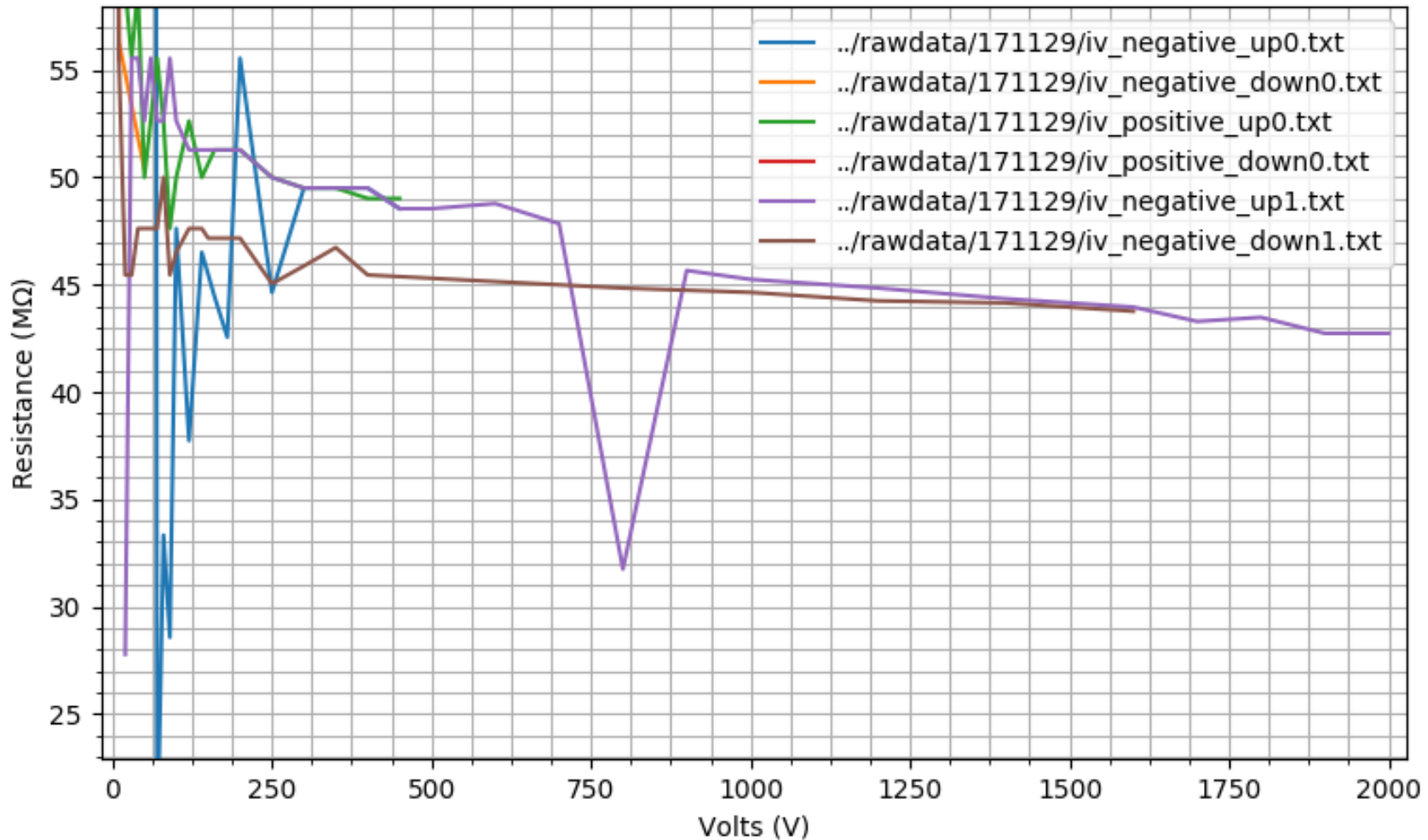


Detailed Steps From Tile 21

- 1) Adjust temperature of manifold to permit flow of cesium while minimizing outgassing
- 2) Measure I-V characteristic of tile
- 3) Scrub
- 4) Measure I-V characteristic of tile
- 5) Heat the tile to 120 C to permit flow of cesium and photocathode formation
- 6) Measure I-V characteristic of tile
- 7) Apply 120 V DC bias across tile
- 8) Admit cesium while measuring photosensitivity at 405 nm
- 9) Stop admitting cesium when?

I-V Characteristic Before Scrubbing



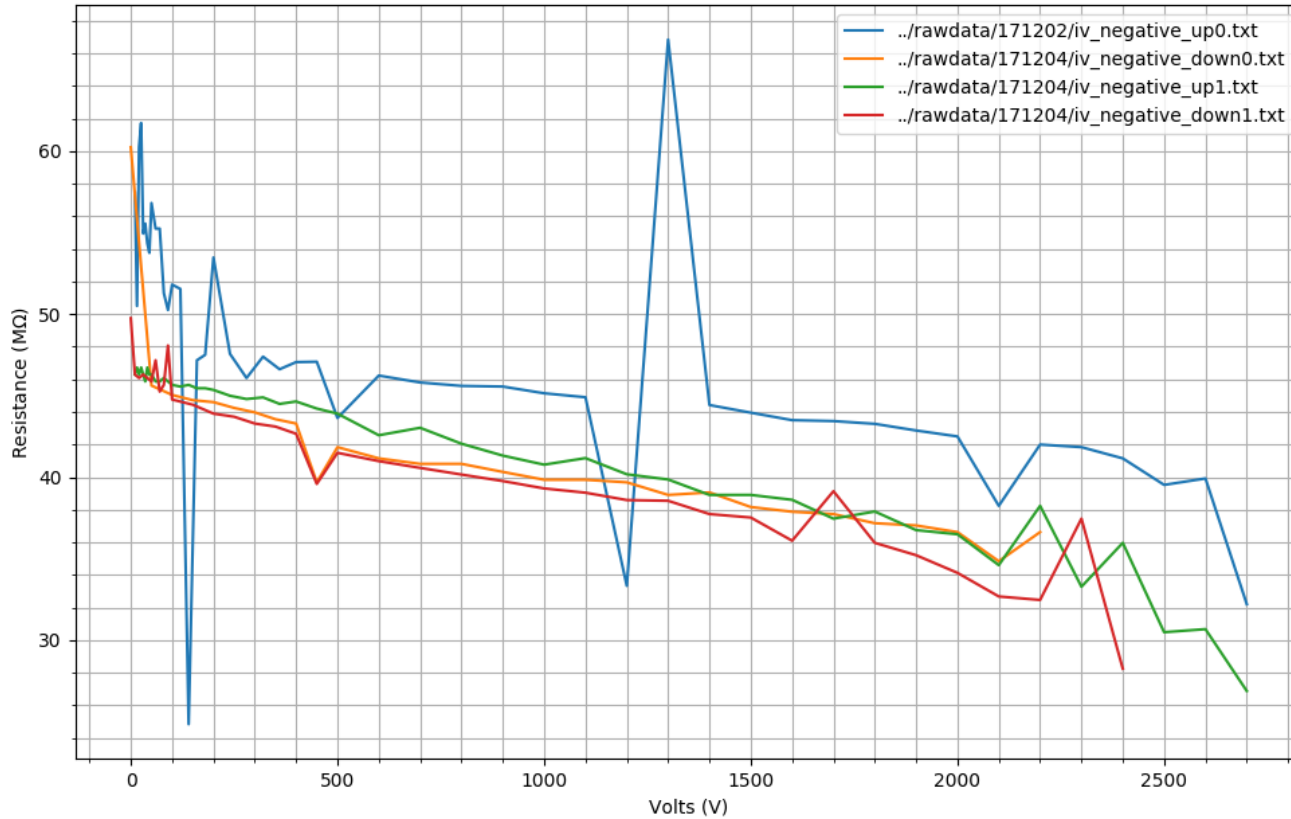
Plot shows dV/dI vs V

Scrub

- Illuminated tile with a small mercury vapor lamp while bias voltage was 1750 V
- Current draw was ~135 microamps, slightly decreasing with time
- Uniform illumination achieved by dithering lamp



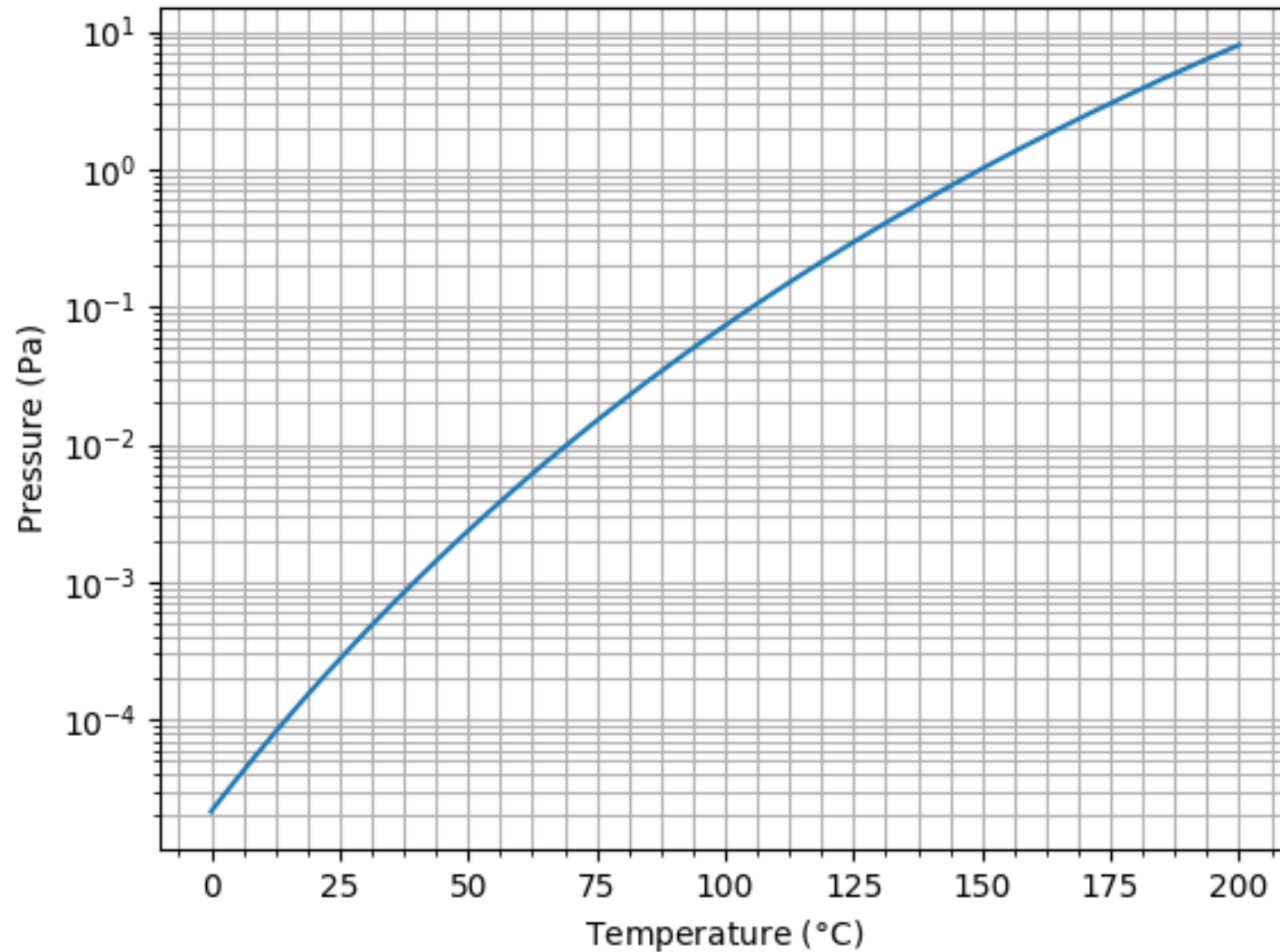
I-V Characteristic After Scrubbing



Slight drop in stack resistance was observed after scrubbing

Heat tile to 115 C

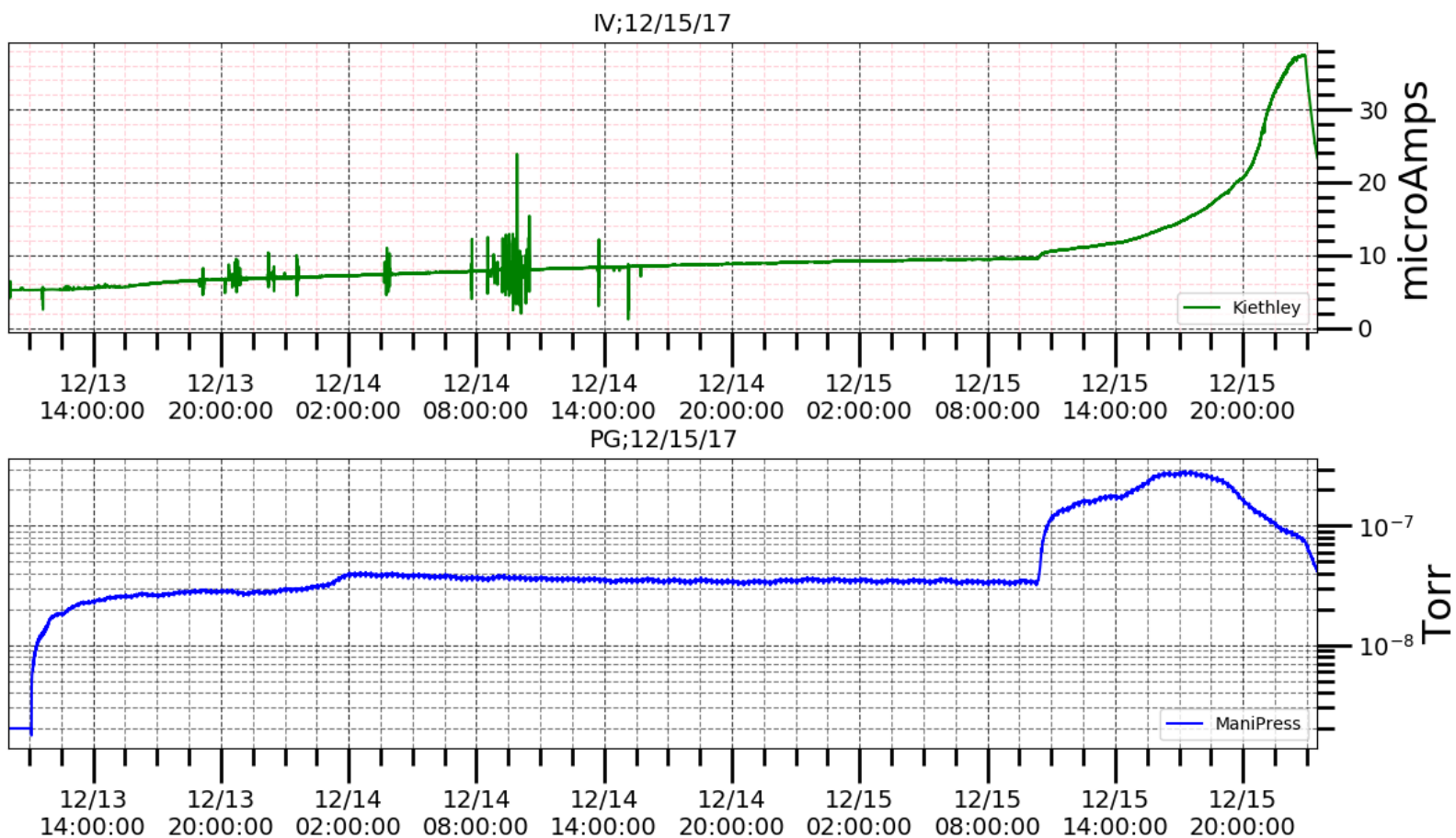
Saturation vapor pressure of Cs as a function of temperature



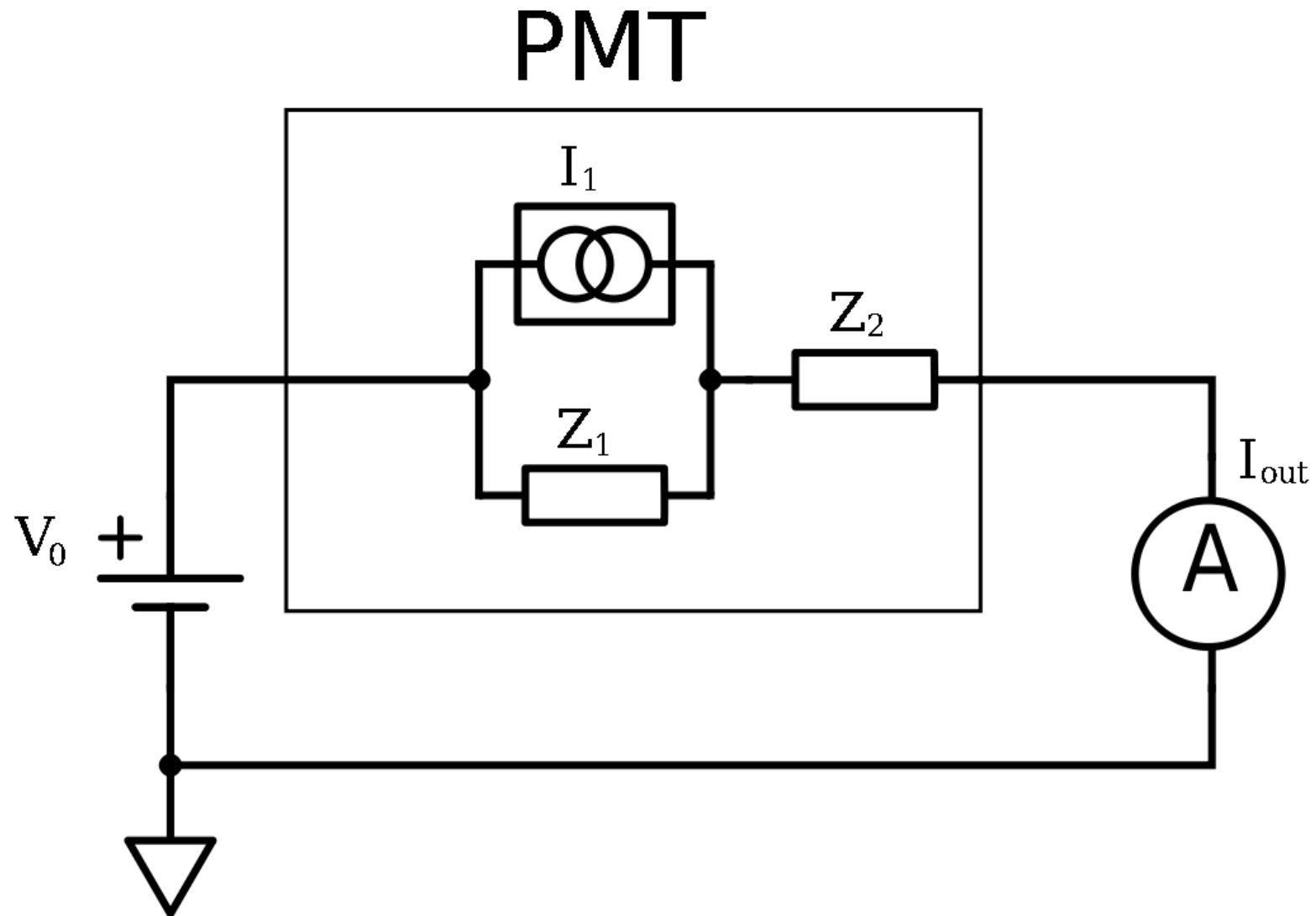
I-V Characteristic With Tile Hot

- Stack resistance dropped from 45 to 24 MOhm
- Internal resistors known to have a much smaller temperature coefficient compared to MCPs
- I-V characteristic was thought to be useful for assessing the behavior of the MCPs while the tile was still hot
- Since then, we have learned that the internal resistors are degraded by Cs, so the stack resistance is less informative

Admit Cs



Resistive Divider Factor



Simple-minded Improvements to Tile 21 Procedure

- Use feedthroughs instead of internal resistors; we have tested the electrode scheme in Tile 23 and 24
- Measure QE of photocathode, since internal resistors no longer interfere
- Use distilled Cs in a copper tube for improved reliability of Cs flow
- Calculate/calibrate conductance to tile from Cs source and keep a Cs budget (estimate is $\sim 5 \times 10^{-3}$ L/s)